

10A Low Barrier Diode

■ Features

- · Low forward voltage drop.
- Excellent high temperature stability.
- Fast switching capability.
- Suffix "G" indicates Halogen-free part, ex.CS10100CTG.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228

■ Mechanical data

• Epoxy: UL94-V0 rated flame retardant.

• Case: JEDEC TO-220AB molded plastic body.

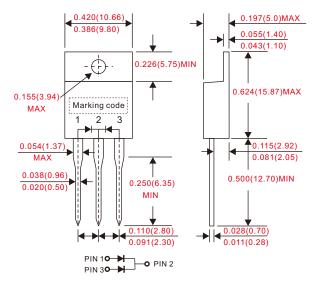
• Terminals : Solder plated, solderable per MIL-STD-750, Method 2026.

Polarity: As marked.Mounting Position : Any.

• Weight: Approximated 2.25 gram.

Outline

TO-220AB



Dimensions in inches and (millimeters)

■ Maximum ratings and electrical characteristics

Rating at 25° C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Conditions	Symbol	CS10100CT	UNIT
Marking code			CS10100CT	
Peak repetitive reverse voltage		V _{RRM}		
Working peak reverse voltage		V _{RWM}	100	V
DC blocking voltage		V _{RM}		
Forward rectified current (total device)		I _o	10	Α
Forward surge current (per diode)	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I _{FSM}	120	Α
Peak repetitive reverse surge current (per diode)	2us - 1kHz	I _{RRM}	2	А
Thermal resistance(1) (per diode)	Junction to case	R _{eJC}	2	°C/W
Operating and Storage temperature		T _J , T _{STG}	-65 ~ +150	°C

Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	UNIT
I Forward voltage drop (per diode)	$I_{F} = 5A, T_{J} = 25^{\circ}C$	V _F			800	mV
	I _F = 5A, T _J = 125°C			640	710	
I Reverse current (per diode)	$V_R = V_{RRM} T_J = 25^{\circ}C$	l _R			0.2	mA
	$V_R = V_{RRM} T_J = 125^{\circ}C$				25	

 $Note: 1. Thermal\ resistance\ from\ junction\ to\ case\ per\ leg,\ with\ heatsink\ size (1.35"\ x\ 0.95"\ x\ 0.18")\ Al-plate.$

Document ID : DS-11K9A Revised Date : 2014/01/22

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■ Rating and characteristic curves

Fig.1 - Forward Current Derating Curve (per diode)

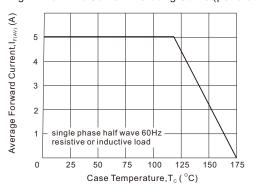


Fig. 2 - Instantaneous Forward Characteristics (per diode)

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T_A=150°C

T_A=125°C

T_A=100°C

T_A=25°C

0.01

0.01

0.01

0.02

0.3

0.4

0.5

0.6

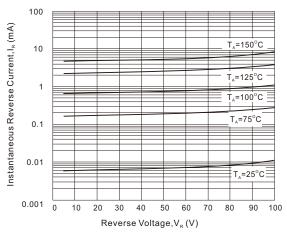
0.7

0.8

0.9

Instantaneous Forward Voltage, $V_{\scriptscriptstyle F}$ (Volts)

Fig. 3 - Reverse Characteristics (per diode)



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Document ID : DS-11K9A Revised Date : 2014/01/22

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